

Atomic and Electronic Structure of the YFeO₃ Surface with Oxygen Vacancies

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Introduction

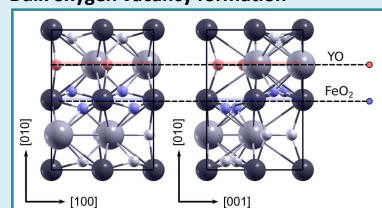
The field of application of the complex oxides with a perovskite structure (ABO₃) is very wide: sensors and detectors, solar cells, photocatalysts and solid oxide fuel cells. It was found that the defect formation in the crystal lattice of ABO₃ leads to a significant increase in catalytic activity, so perovskite compounds can be used as alternative multifunctional catalysts for the neutralizing of diesel gases.

The atomic and electronic structure of YFeO₃ at the formation of oxygen vacancies on the surface was studied using modern computer simulation methods.

Methods and calculation parameters

- Quantum Espresso software package (DFT+ pseudopotential)
- PBE functional
- 6×4×6 k-point grid for orthorhombic YFeO₃ cell
- Cutoff energy – 60 Ry
- Ultrasoft PP for Y, Fe, O from QE database
- Hubbard correction (DFT + U) with the U_{eff} = 4 eV
- Spin-polarization (G-type anti-ferromagnetic order for Fe)

Bulk oxygen vacancy formation



$$E_{form} = E_{vac} - E_{ideal} + \frac{1}{2} E_{O2}$$

Configuration	E _{form} , eV	Difference, eV
YFeO _{3-δ} (δ = 0.25) – O1	3.69	
YFeO _{3-δ} (δ = 0.25) – O2	3.79	0.10
YFeO _{3-δ} (δ = 0.0625) – O1	3.13	
YFeO _{3-δ} (δ = 0.0625) – O2	3.42	0.29

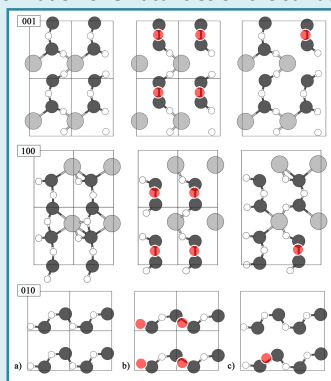
YFeO₃ surfaces: (001), (010) and (100). The formation energies

Surface	Area, m ²	Slab characteristics	Surface energy, J/m ²
(001)	4.36 · 10 ⁻¹⁹	5 layers	0.92
		7 layers	0.91
		5 layers, the lower layers are fixed	0.97
(010)	4.11 · 10 ⁻¹⁹	9 layers (FeO ₂)	1.03
		9 layers (YO)	1.31
		9 layers (FeO ₂), the lower layers are fixed	1.05
(100)	3.01 · 10 ⁻¹⁹	5 layers	1.06
		5 layers, the lower layers are fixed	1.11

- All simplification and number of atomic layers insignificantly influence on the values of surface energy.
- (010)-(FeO₂) surface is more favorable

$$E_{surf} = \frac{E_{unrel,slab} - E_{rel,slab}}{2S}$$

Formation of O vacancies on the surface

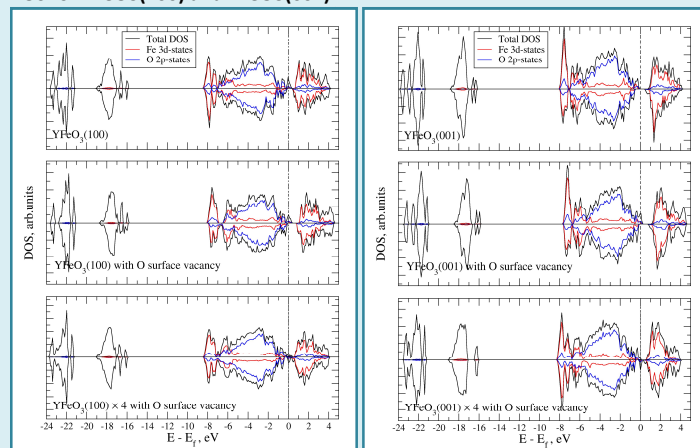


Surface	Area, m ²	E _{form} , eV
(001)	4.36 · 10 ⁻¹⁹	2.40
	17.45 · 10 ⁻¹⁹	1.74
(100)	4.11 · 10 ⁻¹⁹	1.79
	16.44 · 10 ⁻¹⁹	0.81
(010)	3.01 · 10 ⁻¹⁹	3.51
	12.03 · 10 ⁻¹⁹	3.33

$$E_{form} = E_{slab+vac} - E_{slab} + \frac{1}{2} E_{O2}$$

Atoms of YFeO₃ surface layers: a) without oxygen vacancy; b) one vacancy per unit cell cross-section; c) one vacancy per cell area increased by 4 times

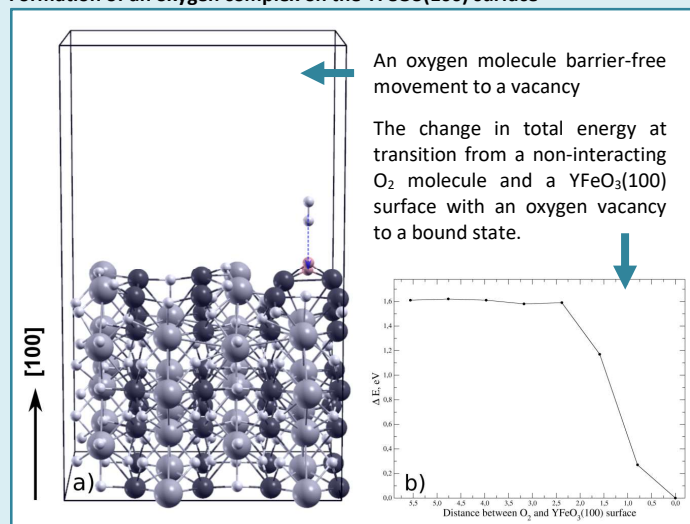
DOS for YFeO3(100) and YFeO3(001)



Formation of an oxygen vacancy leads to the appearance of levels in the band gap, as well as to a partial delocalization of the 3d states of Fe. At the vacancy formation on the YFeO₃(010) surface there are distributed states corresponding to the surface Fe atoms

In the case of the (001) and (100) surfaces there is a partial splitting of the peak corresponding to the bulk states, this occurs due to the formation of the Fe-Fe bond when oxygen is removed from the surface and the surface layers are included in the atomic relaxation process.

Formation of an oxygen complex on the YFeO3(100) surface



An oxygen molecule barrier-free movement to a vacancy

The change in total energy at transition from a non-interacting O₂ molecule and a YFeO₃(100) surface with an oxygen vacancy to a bound state.

Conclusion

- There is a tendency to a decrease in the formation energy with an increase in the surface area, which corresponds to a decrease in the vacancy concentration.
- The smallest value of 0.81 eV was obtained for the (100) surface, which is approximately four times less than the formation energy of a bulk oxygen vacancy.
- An analysis of the electronic structure showed a partial delocalization of the 3d states of Fe atoms at the surface formation process, formation of an oxygen vacancy, due to the appearance of Fe-Fe bond, enhances delocalization effect.
- An oxygen molecule moves to a surface vacancy without barrier. For YFeO₃(100) energy gain of this process is 1.6 eV